



DUAL DECADE COUNTER

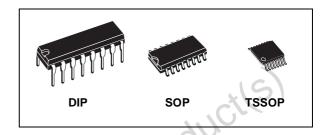
- HIGH SPEED : f_{MAX} = 60 MHz (TYP.) at V_{CC} = 6V
- LOW POWER DISSIPATION: $I_{CC} = 4\mu A(MAX.)$ at $T_A = 25$ °C
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 4518



The M74HC4518 is an high speed CMOS DUAL BINARY COUNTER fabricated with silicon gate C²MOS technology.

It consist of two identical internally synchronous 4-stage counters. The counter stages are D-TYPE flip-flops having interchangeable CLOCK and ENABLE inputs for incrementing on either the positive-going or negative-going transition.

For single-unit operation the ENABLE input is maintained "high" and the counter advances on



ORDER CODES

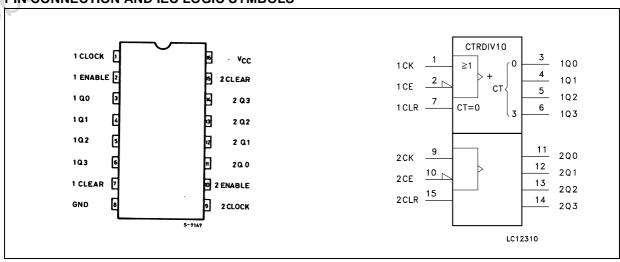
PACKAGE	TUBE	T & R
DIP	M74HC4518B1R	
SOP	M74HC4518M1R	M74HC4518RM13TR
TSSOP		M74HC4518TTR

each positive-going transition of the CLOCK. The counters are cleared by high levels on their clear lines.

The counter can be cascaded in the ripple mode by connecting Q4 to the enable input of the subsequent counter while the clock input of the latter is held permanently low.

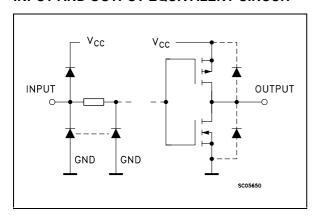
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



July 2001 1/11

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

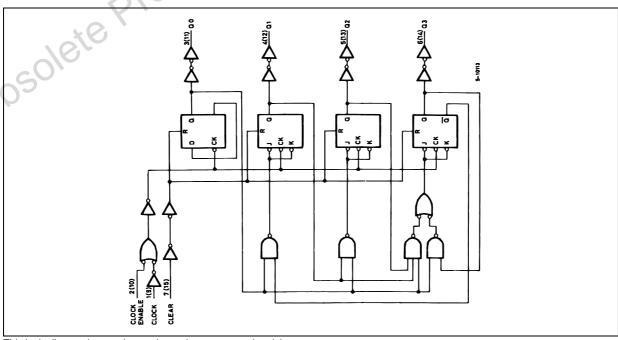
PIN No	SYMBOL	NAME AND FUNCTION
1, 9	1CLOCK, 2CLOCK	Clock Inputs (LOW to HIGH, Edge-Triggered)
2, 10	1ENABLE, 2ENABLE	Clock Enable Inputs
3, 4, 5, 6	1Q0 to 1Q3	Data Outputs
7, 15	1CLEAR, 2CLEAR	Asynchronous Reset Inputs (Active LOW)
11, 12, 13, 14	2Q0 tO 2Q3	Data Outputs
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

TRUTH TABLE

	INPUTS		FUNCTION
CLOCK	ENABLE	CLEAR	FONCTION
	Н	LXO	INCREMENT COUNTER
L	7		INCREMENT COUNTER
Z	X	SUL	NO CHANGE
X	7	L	NO CHANGE
	L	L	NO CHANGE
Н	īle	L	NO CHANGE
X	X	Н	Q0 THRU Q3=L

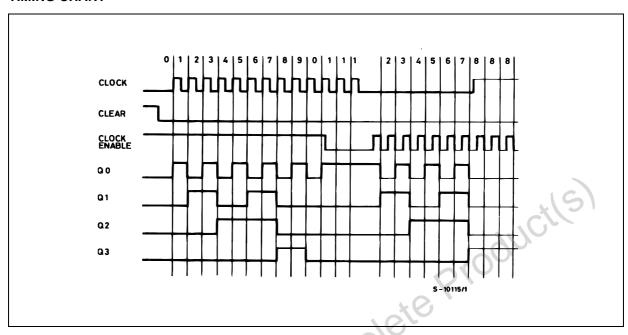
X : Don't Care Z : High Impedance

LOGIC DIAGRAM



This logic diagram has not be used to estimate propagation delays

TIMING CHART



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage		2 to 6	V
V _I	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	V _{CC} = 2.0V	0 to 1000	ns
t _r , t _f		$V_{CC} = 4.5V$	0 to 500	ns
		V _{CC} = 6.0V	0 to 400	ns

DC SPECIFICATIONS

		7	Test Condition				Value		ΛĠ		
Symbol	Parameter	v _{cc}		T,	T _A = 25°C			-40 to 85°C		-55 to 125°C	
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15		*6	3.15		3.15		V
		6.0		4.2	16		4.2		4.2		
V_{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0		V		1.8		1.8		1.8	
V _{OH}	High Level Output	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		
	Voltage	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		V
		4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
	40.	6.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =4.0 mA		0.17	0.26		0.37		0.40	
		6.0	I _O =5.2 mA		0.18	0.26		0.37		0.40	
	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

		1	est Condition				Value		Value						
Symbol	Parameter	V _{cc}	T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit					
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.					
t _{TLH} t _{THL}	Output Transition	2.0			30	75		95		110					
	Time	4.5			8	15		19		22	ns				
		6.0			7	13		16		19					
t _{PLH} t _{PHL}	Propagation Delay	2.0			72	160		200		240					
	Time	4.5			22	32		40		48	ns				
	(CK, ENABLE - Qn)	6.0			18	27		34		41					
t _{PHL}	Propagation Delay	2.0			65	150		190		225					
	Time	4.5			20	30		38		45	ns				
	(CLR - Qn)	6.0			16	26		33		38	,				
f _{MAX}	Maximum Clock	2.0		6	23		4.8		4						
	Frequency	4.5		30	51		24		20		MHz				
		6.0		35	60		28	O_{\sim}	24						
t _{W(H)}	Minimum Pulse	2.0			25	75		95		110					
t _{W(L)}	Width	4.5			6	15		19		22	ns				
	(CLOCK ,ENABLE)	6.0			5	13		16		19					
t _{W(L)}	Minimum Pulse	2.0			20	75		95		110					
	Width	4.5		C	5	15		19		22	ns				
	(CLEAR)	6.0		0-	4	13		16		19					
t _{REM}	Minimum Removal	2.0			21	50		60		75					
	Time	4.5			3	10		12 15	ns						
	(CLEAR)	6.0			3	9		11		13					

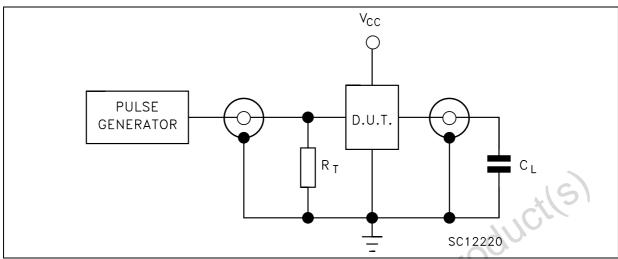
CAPACITIVE CHARACTERISTICS

		Test Condition		Value							
Symbol	bol Parameter	V _{CC}		T _A = 25°C -40 to 85°C		-55 to 125°C		Unit			
		(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)				38						pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/2$ (per Counter)

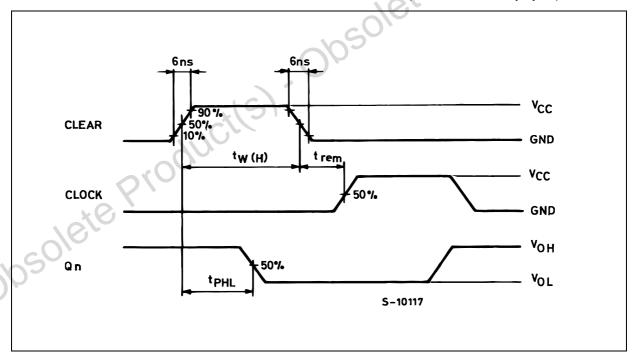
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TEST CIRCUIT

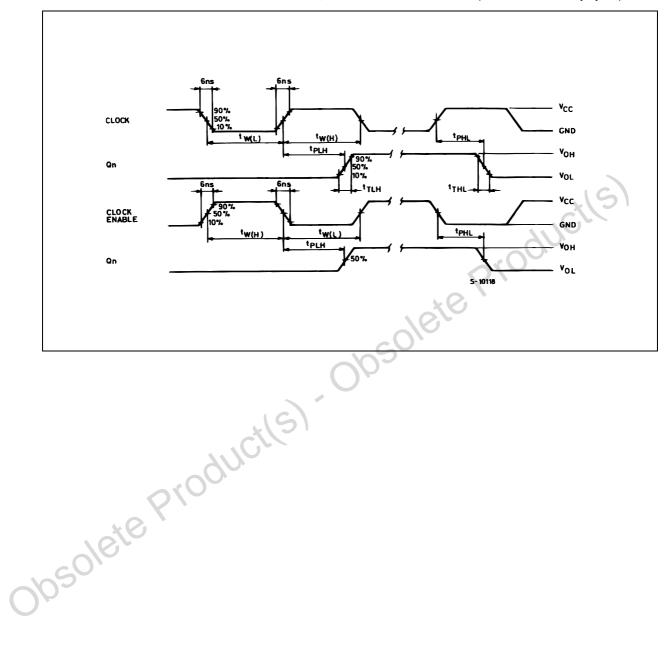


 C_L = 50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1: MINIMUM PULSE WIDTH AND REMOVAL TIME (f=1MHz; 50% duty cycle)

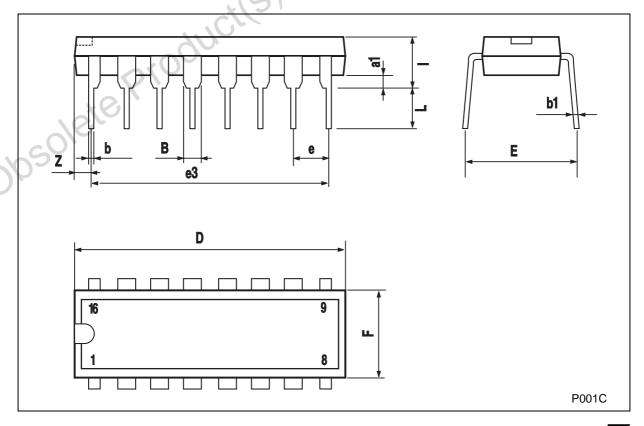


WAVEFORM 2: PROPAGATION DELAY TIME, MINIMUM PULSE WIDTH (f=1MHz; 50% duty cycle)



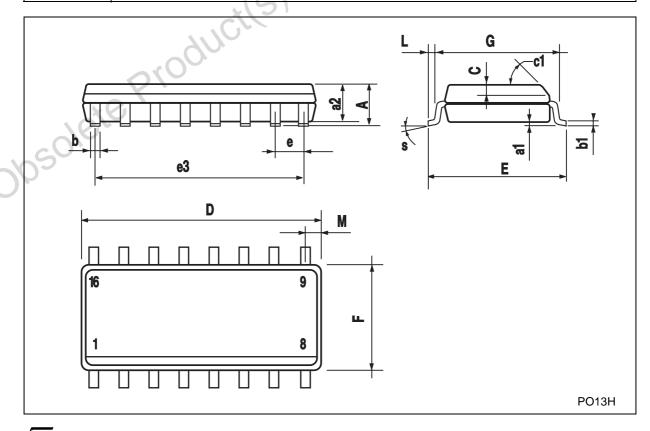
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM	mm.				inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
a1	0.51			0.020					
В	0.77		1.65	0.030		0.065			
b		0.5			0.020				
b1		0.25			0.010	19			
D			20		.(0.787			
E		8.5			0.335				
е		2.54			0.100				
e3		17.78		× (2)	0.700				
F			7.1	7/6/		0.280			
1			5.1	0.		0.201			
L		3.3	Oh		0.130				
Z			1.27			0.050			



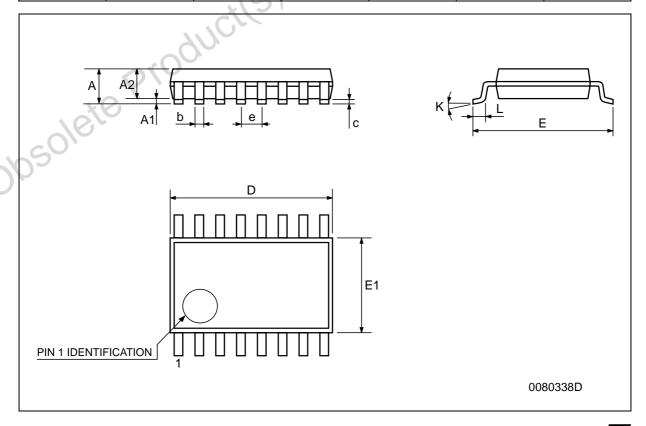
SO-16 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	1191
c1			45° (typ.)	.(-11
D	9.8		10	0.385	70	0.393
E	5.8		6.2	0.228	400	0.244
е		1.27			0.050	
e3		8.89		8	0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S		10	8° (n	nax.)		



TSSOP16 MECHANICAL DATA

DIM.		mm.		inch				
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004	401	0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
Е	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC	-105	0,	0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		





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